EPISTAR

ES-VAGHA18A

InGaN A-series Green LED Chip

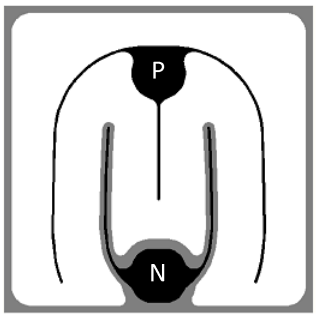
> Mechanical Specification:

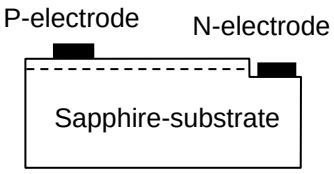
(1) Dimension
- Chip size: 457 ± 25 μm x 457 ± 25 μm
- Thickness: 150 ± 10 μm
- P bonding pad: 90 ± 10 μm
- N bonding pad: 90 ± 10 μm

(2) Metallization
- Topside P electrode: Au alloy
- Topside N electrode: Au alloy

Features:
- High radiant flux
- Long operation life

Applications:
- Automotive





> Electro-optical Characteristics at 25°C: (1)

Parameter	Symbol		Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf1		If = 10μA	1.6	-	-	V
	Vf2		If = 120mA	-	3.1	3.3	V
Reverse Current	Ir		Vr = 5V	-	-	1.0	μA
Dominant Wavelength(2)	λd		If = 120mA	515	-	535	nm
Spectra Half-width	Δλ		If = 120mA	-	35	-	nm
Radiant Flux(3)(4)	Po	A50	If = 120mA	80	-	85	mW
		A51		85	-	90	
		A52		90	-	95	
		A53		95	-	100	

Note:
(1) ESD protection during chip handling is recommended.
(2) Basically, the wavelength span is 20nm; however, customers' special requirements are also welcome.
(3) Radiant flux is determined by using an Ag-plated TO-can header without an encapsulant.
(4) Radiant flux measurement allows a tolerance of ±15%.

> Absolute Maximum Ratings:

Parameter	Symbol	Condition	Rating	Unit
Forward DC Current	If	Ta = 25˚C	≤ 200	mA
Reverse Voltage	Vr	Ta = 25˚C	≤ 5	V
Junction Temperature	Tj	-	≤ 125	˚C
ESD withstand voltage(HBM)(2)	V_{ESD}	-	Up to 2	KV
Storage Temperature	Tstg	Chip	-40 ~ +85	˚C
		Chip-on-tape/storage	5 ~ 35	˚C
		Chip-on-tape/transportation	-20 ~ +65	˚C
Temperature during Packaging	-	-	280(<10sec)	˚C

Note: (1) Maximum ratings are package dependent. The above maximum ratings were determined using a Printed Circuit Board (PCB) without an encapsulant. Stresses in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.
(2) According to ANSI/ESDA/JEDEC JS-001

> Characteristic Curves:

Fig.1 – Relative luminous Intensity vs. Forward Current

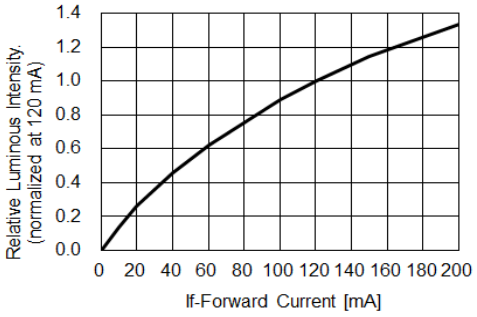


Fig.2 – Forward Current vs. Forward Voltage

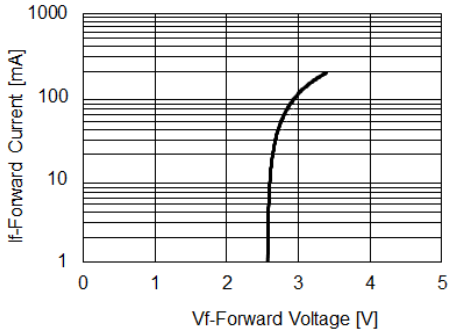


Fig.3 – Relative Intensity (@120mA) vs. Ambient Temperature

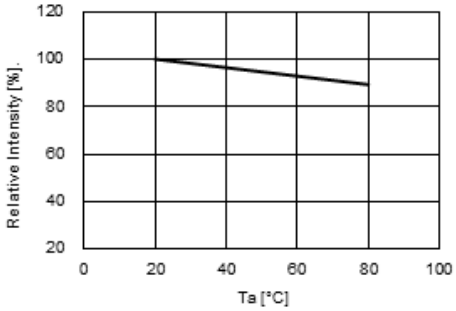


Fig.4 – Forward Voltage (@120mA) vs. Ambient Temperature

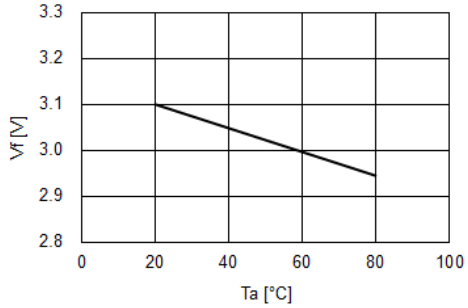


Fig.5 – Dominant Wavelength (@120mA) vs. Ambient Temperature

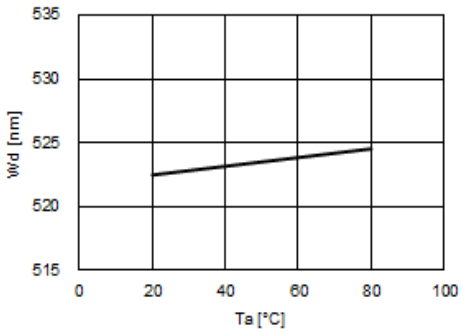
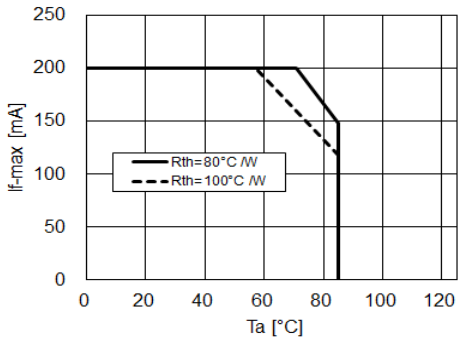


Fig.6 – Maximum Driving Forward DC Current vs. Ambient Temperature (De-rating based on Tj max. = 125°C)



> Qualification:

[1] EPISTAR's LED chips and epi-wafers are designed and manufactured according to the quality management system that complies to the IATF 16949:2016 requirements (IATF No: 0325277/ Certificate Registration No: 20000910 IATF 16).

[2] The chip qualification test plan is based on the guidelines of AEC-Q101-REV-D, Failure Mechanism Based Stress Test Qualification for Discrete Semiconductors in Automotive Applications.

> Revision:

Version	Page	Subjects	Date of Modification
A	3	Initial Release	December. 2018